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[VS-16EDH02HM3](#)

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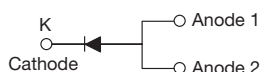
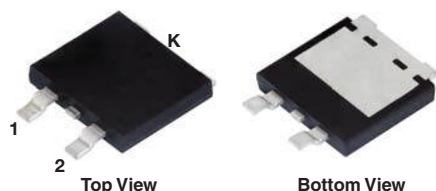


www.vishay.com

VS-16EDH02HM3

Vishay Semiconductors

Hyperfast Rectifier, 16 A FRED Pt®



FEATURES

- Hyperfast recovery time, reduced Q_{rr} , and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, telecom, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

PRODUCT SUMMARY

| | |
|-----------------|-----------------|
| Package | TO-263AC (SMPD) |
| $I_{F(AV)}$ | 16 A |
| V_R | 200 V |
| V_F at I_F | 0.75 V |
| t_{rr} | 32 ns |
| T_J max. | 175 °C |
| Diode variation | Single die |

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
|-----------------------------------|-------------|--|--------|-------|
| Peak repetitive reverse voltage | V_{RRM} | | 200 | V |
| Average rectified forward current | $I_{F(AV)}$ | $T_{solder\ pad} = 152\text{ °C}$ | 16 | A |
| Non-repetitive peak surge current | I_{FSM} | $T_J = 25\text{ °C}$, 6 ms square pulse | 250 | |

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|-------------------------------------|---------------|---|------|------|------|---------------|
| Breakdown voltage, blocking voltage | V_{BR}, V_R | $I_R = 100\text{ }\mu\text{A}$ | 200 | - | - | V |
| Forward voltage | V_F | $I_F = 16\text{ A}$ | - | 0.91 | 1.0 | |
| | | $I_F = 16\text{ A}$, $T_J = 150\text{ °C}$ | - | 0.75 | 0.84 | |
| Reverse leakage current | I_R | $V_R = V_R$ rated | - | - | 15 | μA |
| | | $T_J = 150\text{ °C}$, $V_R = V_R$ rated | - | 20 | 500 | |
| Junction capacitance | C_T | $V_R = 200\text{ V}$ | - | 60 | - | pF |



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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) | | | | | | |
|---|-----------|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Reverse recovery time | t_{rr} | $I_F = 1\text{ A}$, $dI_F/dt = 50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$ | - | 32 | - | ns |
| | | $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{rr} = 0.25\text{ A}$ | - | - | 32 | |
| | | $T_J = 25^\circ\text{C}$ | - | 26 | - | |
| | | $T_J = 125^\circ\text{C}$ | - | 40 | - | |
| Peak recovery current | I_{RRM} | $T_J = 25^\circ\text{C}$ | - | 2.8 | - | A |
| | | $T_J = 125^\circ\text{C}$ | - | 6 | - | |
| Reverse recovery charge | Q_{rr} | $T_J = 25^\circ\text{C}$ | - | 37 | - | nC |
| | | $T_J = 125^\circ\text{C}$ | - | 125 | - | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|----------------|----------------------------|---------|------|------|---------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T_J, T_{Stg} | | -55 | - | +175 | $^\circ\text{C}$ |
| Thermal resistance, junction to solder pad | R_{thJ-Sp} | | - | 1.1 | 1.5 | $^\circ\text{C}/\text{W}$ |
| Approximate weight | | | 0.55 | | | g |
| | | | 0.02 | | | oz. |
| Marking device | | Case style TO-263AC (SMPD) | 16EDH02 | | | |

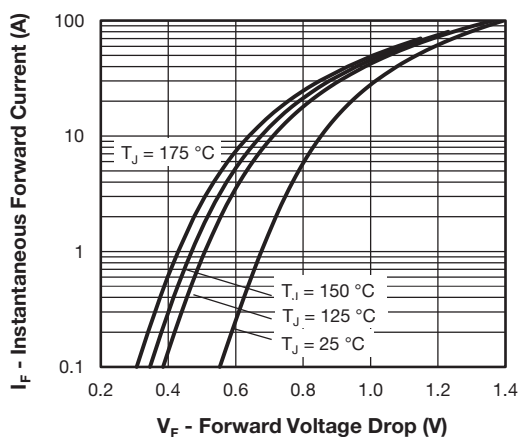


Fig. 1 - Typical Forward Voltage Drop Characteristics

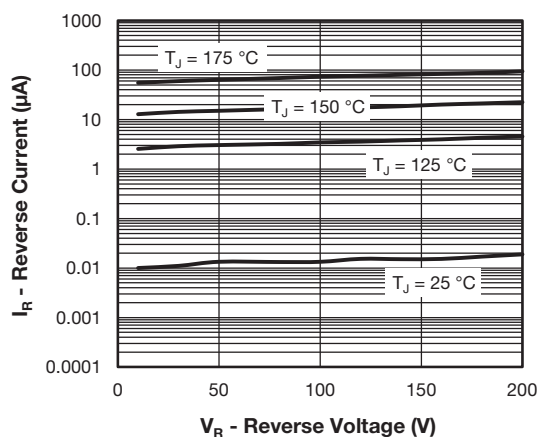


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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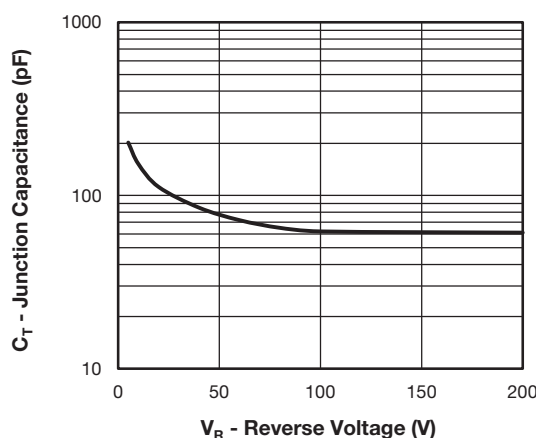


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

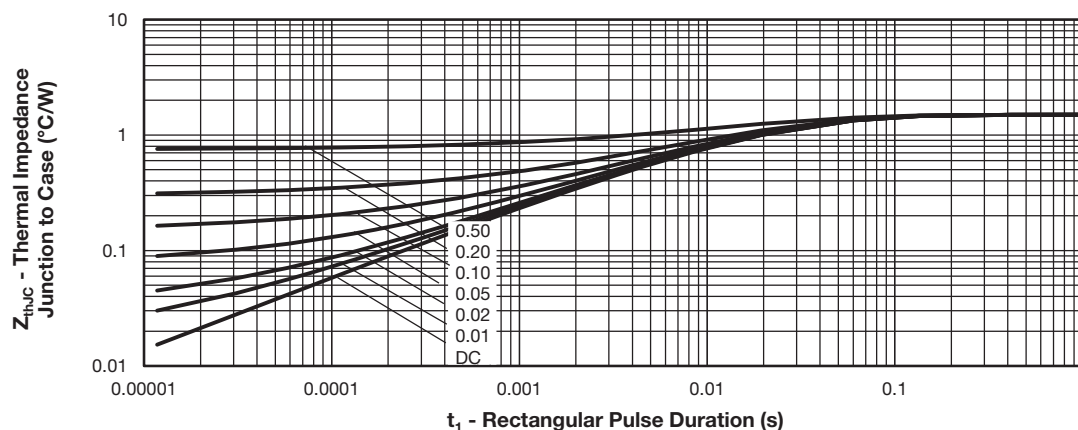


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

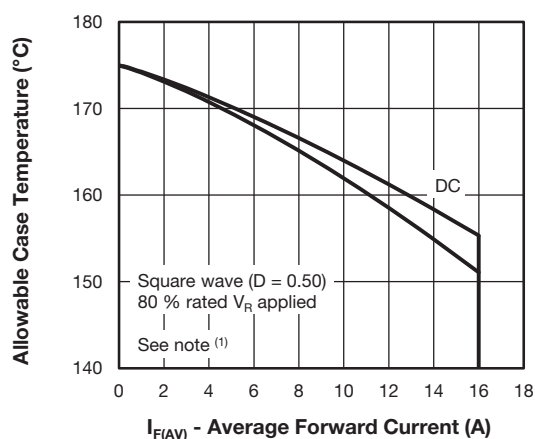


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

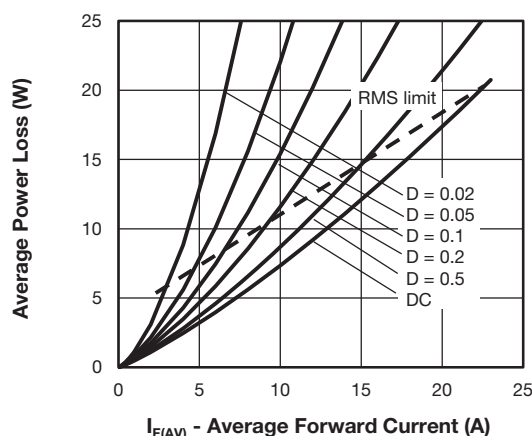


Fig. 6 - Forward Power Loss Characteristics

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5);
 P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R



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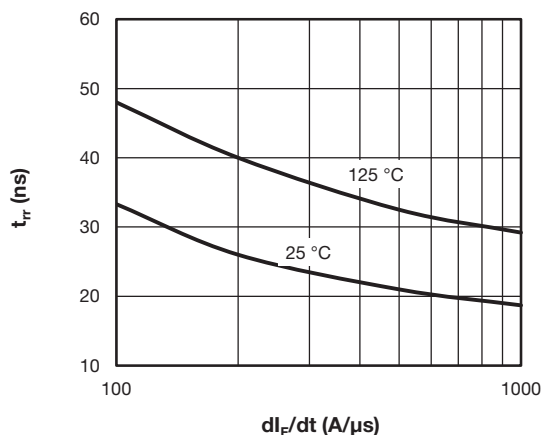


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

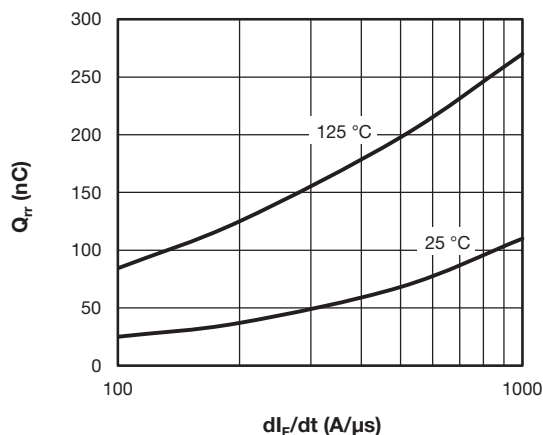


Fig. 8 - Typical Stored Charge vs. dI_F/dt

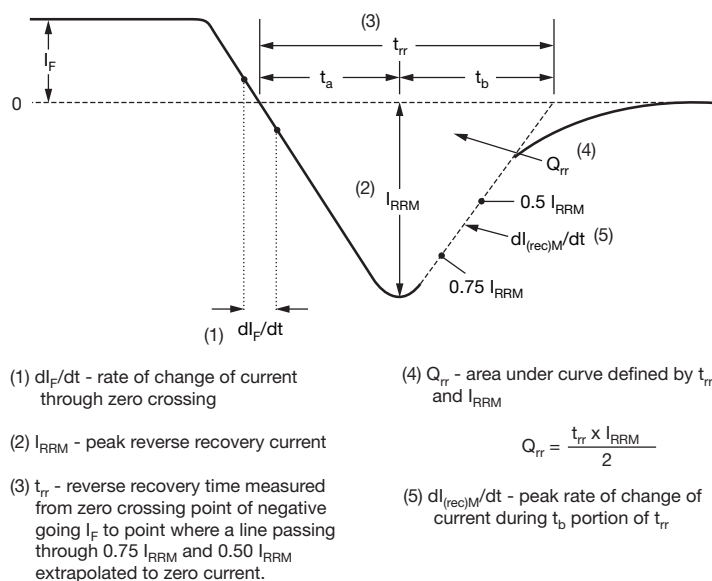


Fig. 9 - Reverse Recovery Waveform and Definitions



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